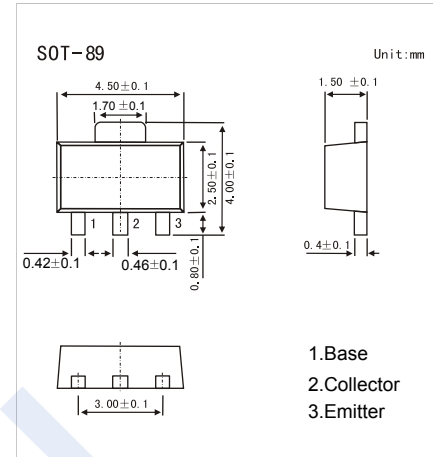


PNP Transistors

2SB1119

■ Features

- Very small size making it easy to provide high density, small-sized hybrid IC's.
- Complementary to 2SD1619



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	-25	V
Collector - Emitter Voltage	V _{CEO}	-25	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-1	A
Collector current -Pulse	I _{CP}	-2	
Collector Power Dissipation (Note.1)	P _C	0.5 1.3	W
Junction Temperature	T _J	150	
Storage Temperature range	T _{stg}	-55 to 150	

Note.1: Mounted on ceramic board (250mm² × 0.8mm)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μA, I _E =0	-25			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, R _{BE} =∞	-25			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C =0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -20V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500 mA, I _B =-50mA		-0.15	-0.7	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-500 mA, I _B =-50mA		-0.85	-1.2	
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -50 mA	100		560	
		V _{CE} = -2V, I _C = -1 A	40			
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		25		pF
Transition frequency	f _T	V _{CE} = -10V, I _C = -50mA		180		MHz

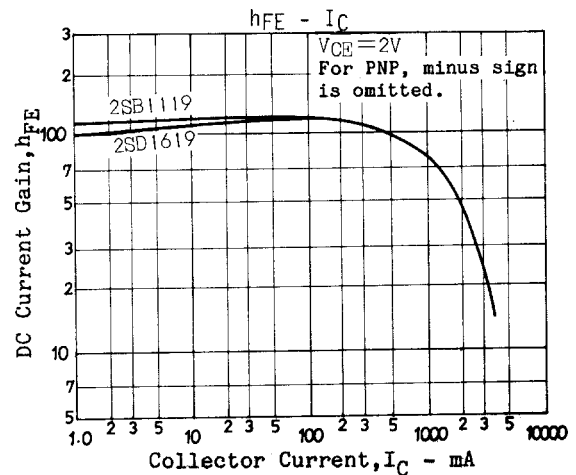
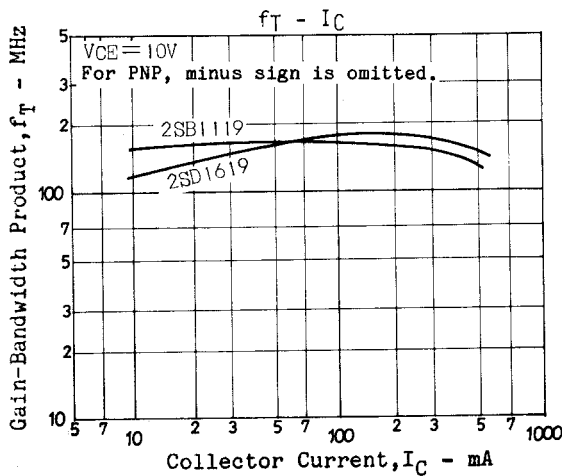
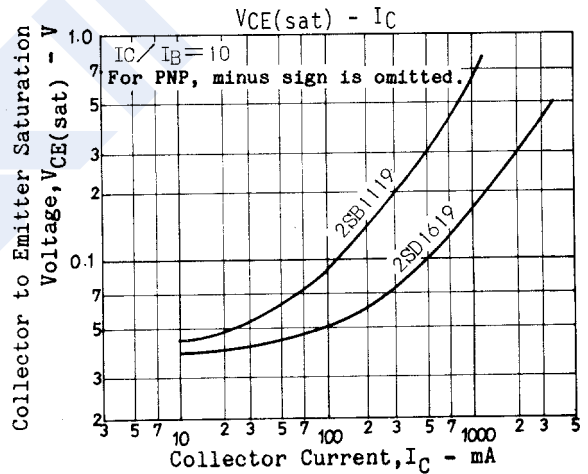
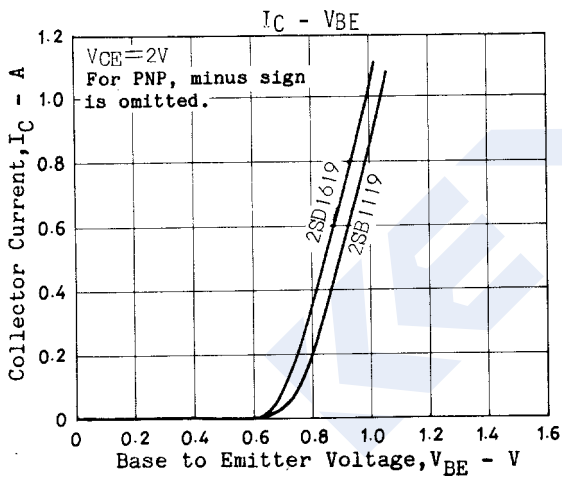
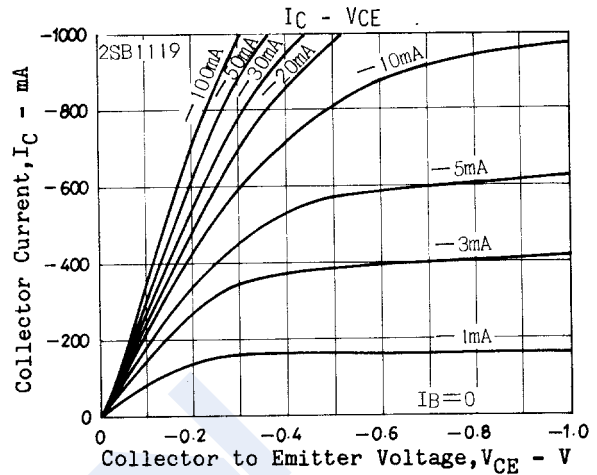
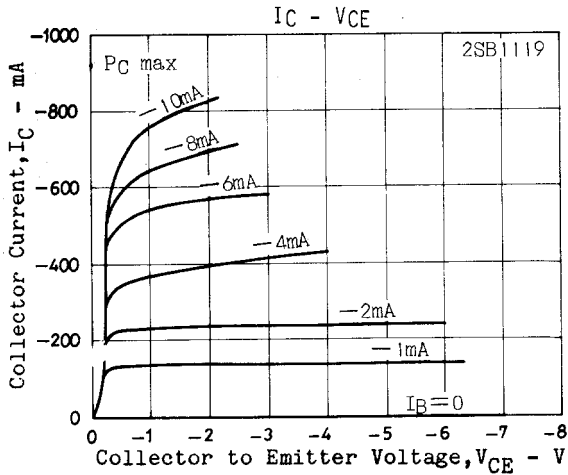
■ Classification of h_{FE}(1)

Type	2SB1119-R	2SB1119-S	2SB1119-T	2SB1119-U
Range	100-200	140-280	200-400	280-560
Marking	BB R*	BB S*	BB T*	BB U*

PNP Transistors

2SB1119

■ Typical Characteristics



PNP Transistors

2SB1119

■ Typical Characteristics

